

# BSS87

200 V, N-channel vertical D-MOS transistor

9 December 2014

Product data sheet

## 1. General description

N-channel enhancement mode vertical Double-Diffused Field-Effect Transistor (D-MOSFET) in a SOT89 (SC-62) medium power and flat lead Surface-Mounted Device (SMD) plastic package.

## 2. Features and benefits

- Direct interface to Complementary (C-MOS) transistor and Transistor-Transistor Logic (TTL) devices.
- Very fast switching
- No secondary breakdown

## 3. Applications

- Relay driver
- High-speed line driver
- Load-side loadswitch
- Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j = 25\text{ °C}$	-	-	200	V
$V_{GS}$	gate-source voltage		-20	-	20	V
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	0.4	A
<b>Static characteristics</b>						
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 0.4\text{ A}; T_j = 25\text{ °C}$	-	1.6	3	$\Omega$

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

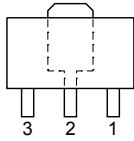
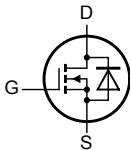


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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p style="text-align: center;"><b>SOT89</b></p>	 <p style="text-align: center;"><i>017aaa253</i></p>
2	D	drain		
3	G	gate		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BSS87	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89

## 7. Marking

Table 4. Marking codes

Type number	Marking code
BSS87	KA

## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j = 25\text{ °C}$		-	200	V
$V_{GS}$	gate-source voltage			-20	20	V
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{amb} = 25\text{ °C}; t \leq 5\text{ s}$	[1]	-	0.7	A
		$V_{GS} = 10\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	0.4	A
		$V_{GS} = 10\text{ V}; T_{amb} = 100\text{ °C}$	[1]	-	0.2	A
$I_{DM}$	peak drain current	$T_{amb} = 25\text{ °C};$ single pulse; $t_p \leq 10\text{ }\mu\text{s}$		-	1.6	A
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ °C}$	[2]	-	0.58	W
			[1]	-	1	W
		$T_{sp} = 25\text{ °C}$		-	12.5	W
$T_j$	junction temperature			-55	150	°C
$T_{amb}$	ambient temperature			-55	150	°C
$T_{stg}$	storage temperature			-65	150	°C
<b>Source-drain diode</b>						
$I_S$	source current	$T_{amb} = 25\text{ °C}$	[1]	-	0.4	A

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

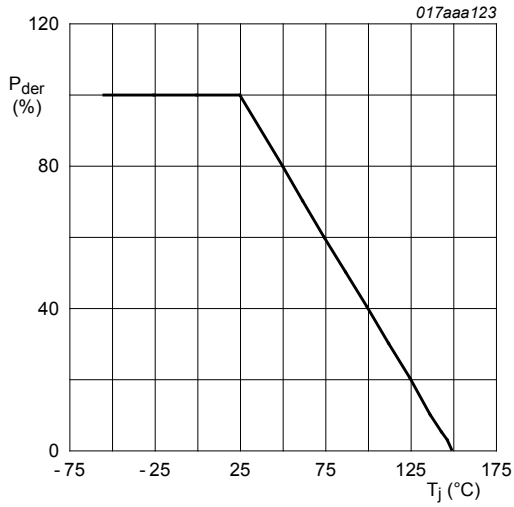


Fig. 1. MOSFET transistor: Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

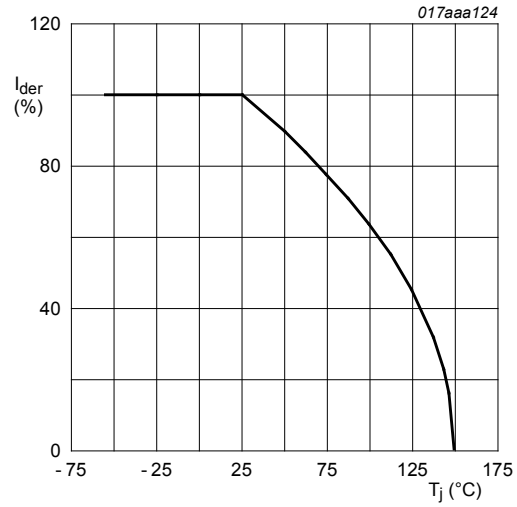
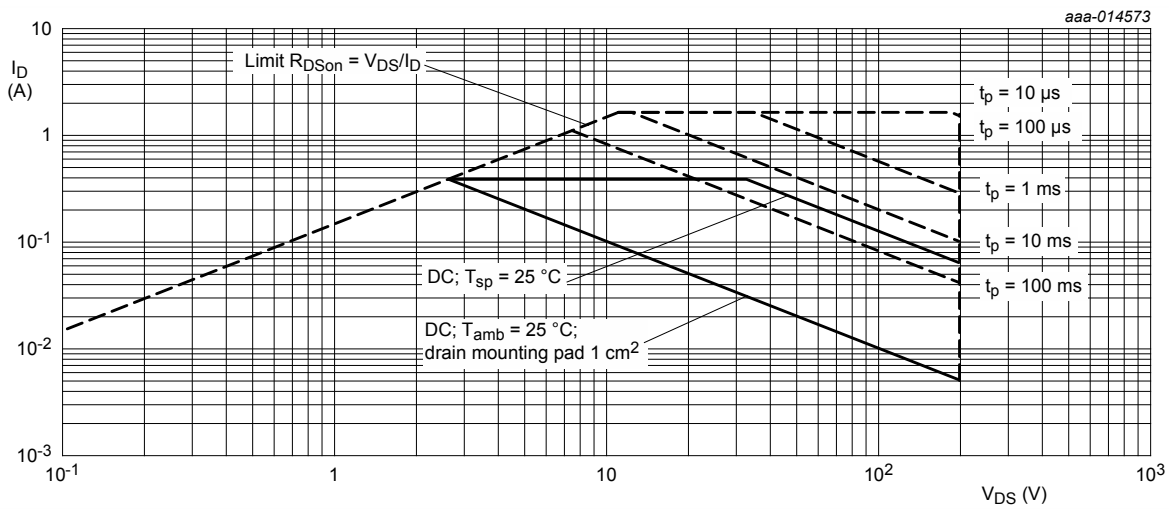


Fig. 2. MOSFET transistor: Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$



I<sub>DM</sub> = single pulse

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	190	216	K/W
			[2]	-	105	125	K/W
		in free air; $t \leq 5$ s	[2]	-	36	42	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	6	10	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

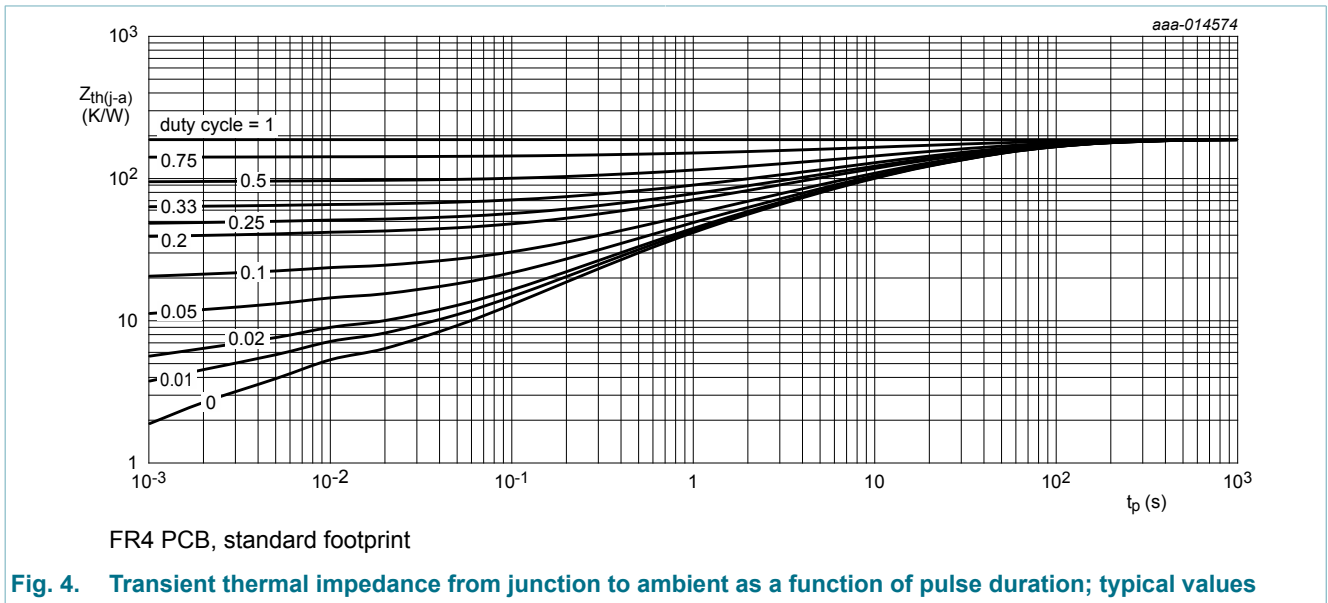
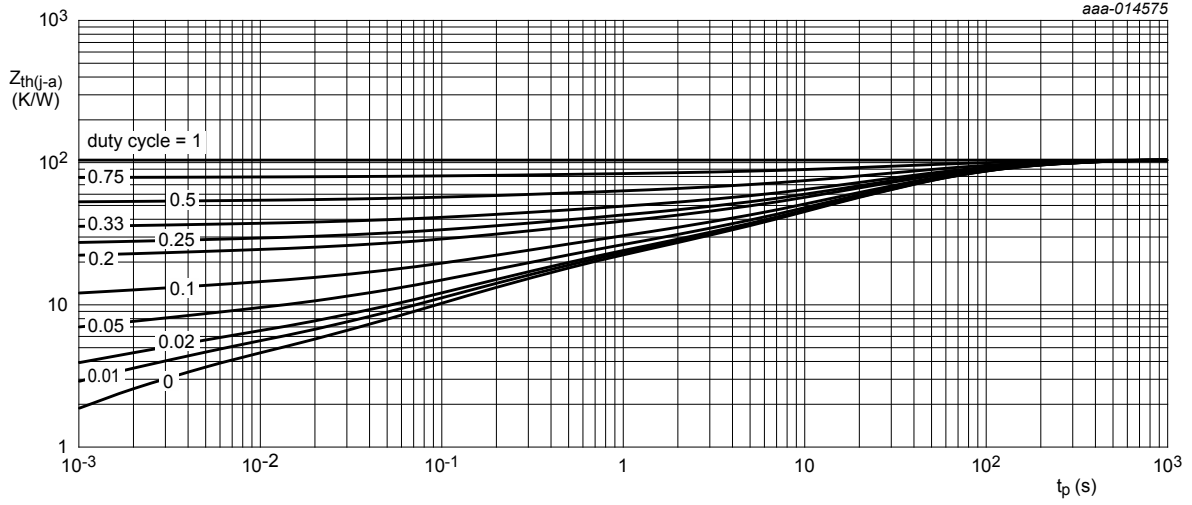


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



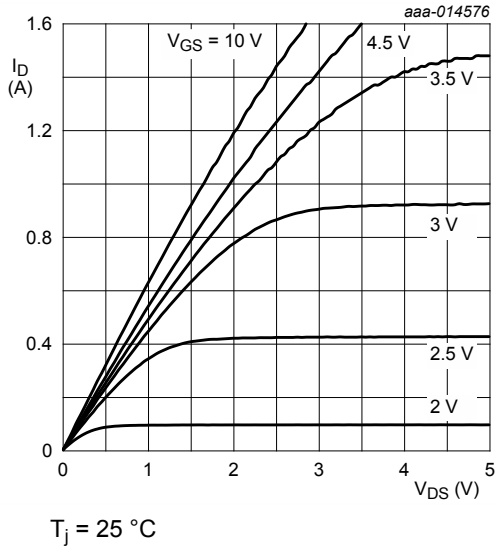
FR4 PCB, mounting pad for drain 1 cm<sup>2</sup>

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

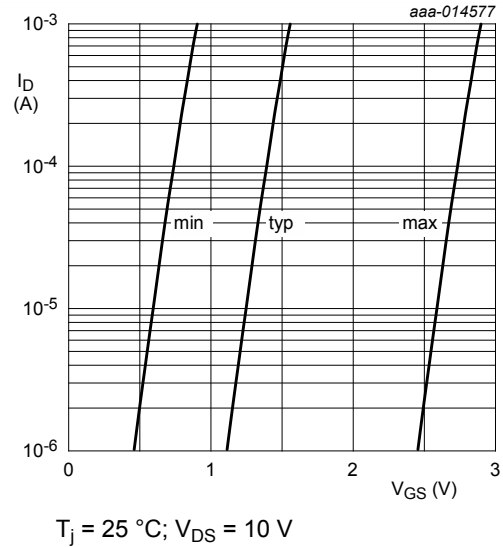
## 10. Characteristics

Table 7. Characteristics

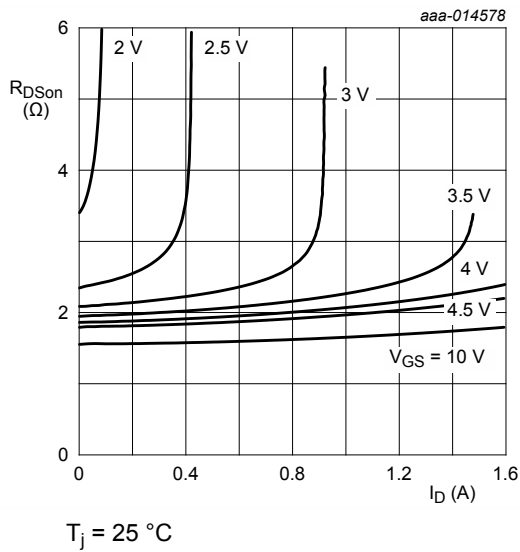
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	200	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	0.8	-	2.8	V
$I_{DSS}$	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	200	nA
		$V_{DS} = 200 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	60	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	-100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 0.4 \text{ A}; T_j = 25 \text{ }^\circ C$	-	1.6	3	$\Omega$
		$V_{GS} = 10 \text{ V}; I_D = 0.4 \text{ A}; T_j = 150 \text{ }^\circ C$	-	3.7	7	$\Omega$
		$V_{GS} = 4.5 \text{ V}; I_D = 0.3 \text{ A}; T_j = 25 \text{ }^\circ C$	-	1.9	4	$\Omega$
$g_{fs}$	forward transconductance	$V_{DS} = 25 \text{ V}; I_D = 0.4 \text{ A}; T_j = 25 \text{ }^\circ C$	-	0.8	-	S
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$V_{DS} = 50 \text{ V}; I_D = 0.25 \text{ A}; V_{GS} = 10 \text{ V}; T_j = 25 \text{ }^\circ C$	-	5.5	10	nC
$Q_{GS}$	gate-source charge		-	0.3	-	nC
$Q_{GD}$	gate-drain charge		-	1.4	-	nC
$C_{iss}$	input capacitance	$V_{DS} = 25 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	100	120	pF
$C_{oss}$	output capacitance		-	20	30	pF
$C_{rss}$	reverse transfer capacitance		-	10	15	pF
$t_{d(on)}$	turn-on delay time		$V_{DS} = 50 \text{ V}; I_D = 0.25 \text{ A}; V_{GS} = 10 \text{ V}; R_{G(ext)} = 6 \text{ } \Omega; T_j = 25 \text{ }^\circ C$	-	2.7	6
$t_r$	rise time	-		3.7	6	ns
$t_{d(off)}$	turn-off delay time	-		16.4	30	ns
$t_f$	fall time	-		7.5	20	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 0.4 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	0.8	1.2	V



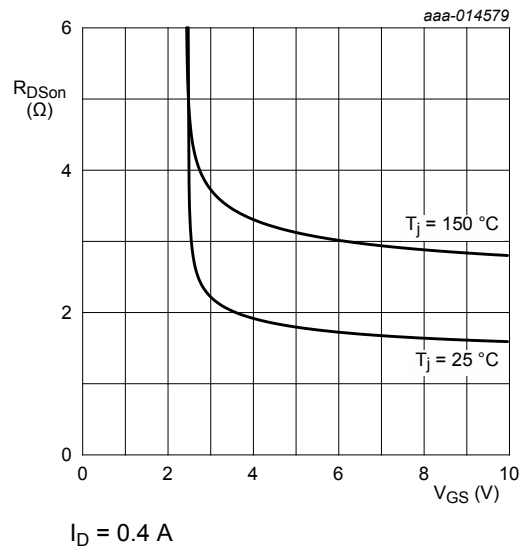
**Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values**



**Fig. 7. Sub-threshold drain current as a function of gate-source voltage**

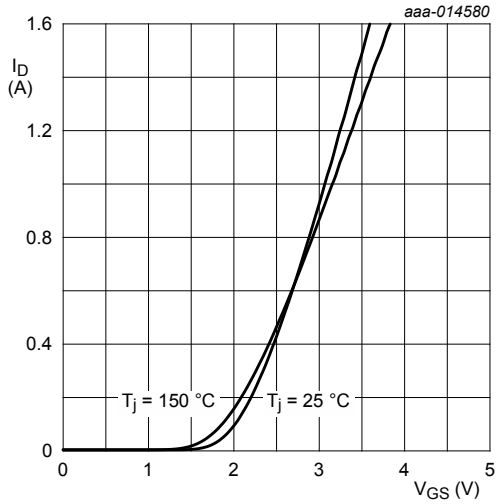


**Fig. 8. Drain-source on-state resistance as a function of drain current; typical values**



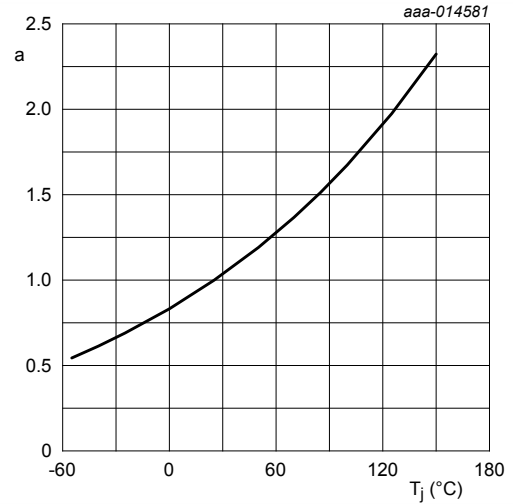
**Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values**





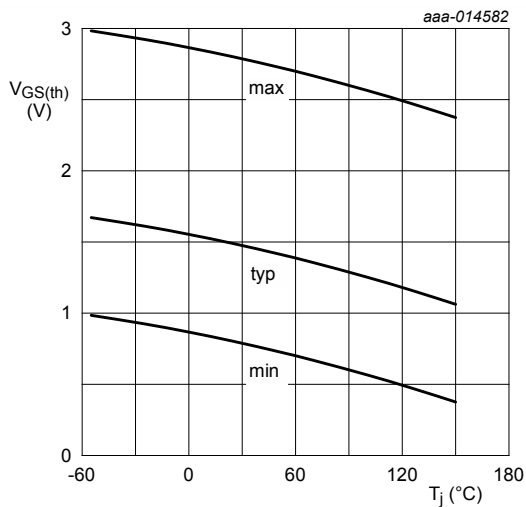
$$V_{DS} > I_D \times R_{DSon}$$

**Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



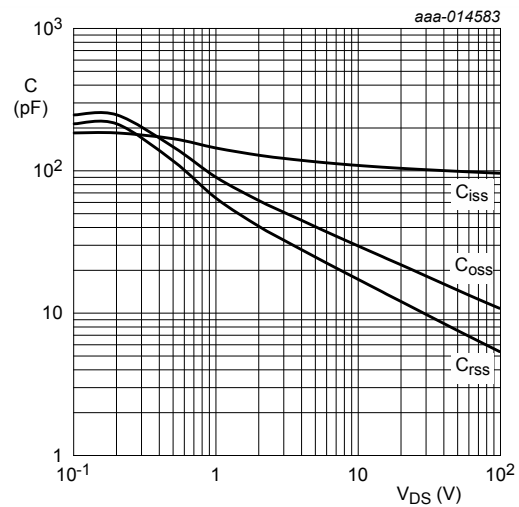
**Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values**

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$



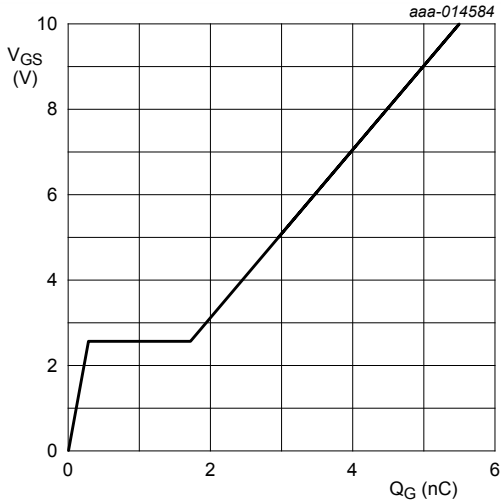
$$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$$

**Fig. 12. Gate-source threshold voltage as a function of junction temperature**



$$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$$

**Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**



$I_D = 0.25 \text{ A}$ ;  $V_{DS} = 50 \text{ V}$ ;  $T_{amb} = 25 \text{ }^\circ\text{C}$

Fig. 14. Gate-source voltage as a function of gate charge; typical values

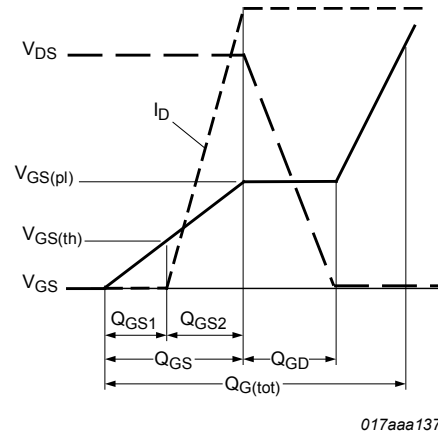
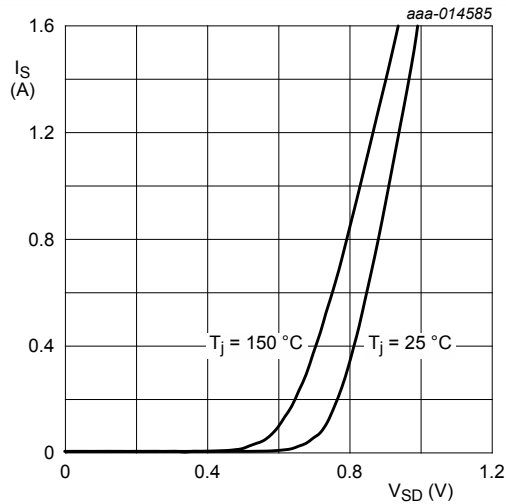


Fig. 15. MOSFET transistor: Gate charge waveform definitions



$V_{GS} = 0 \text{ V}$

Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information

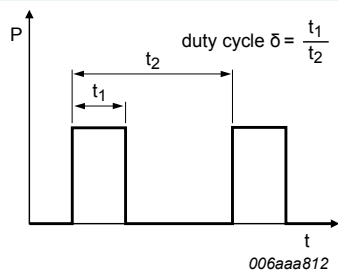


Fig. 17. Duty cycle definition

## 12. Package outline

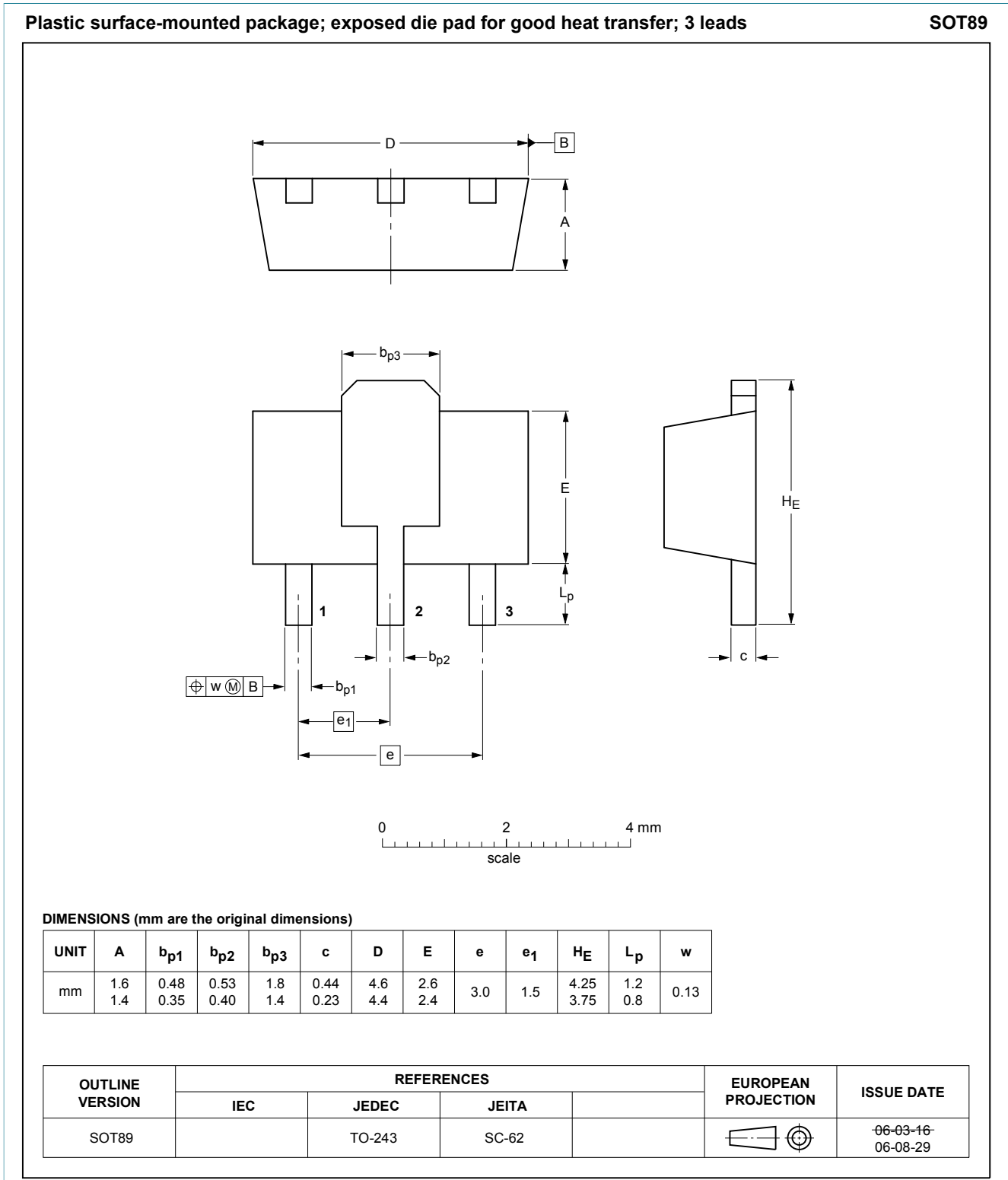


Fig. 18. Package outline SOT89

### 13. Soldering

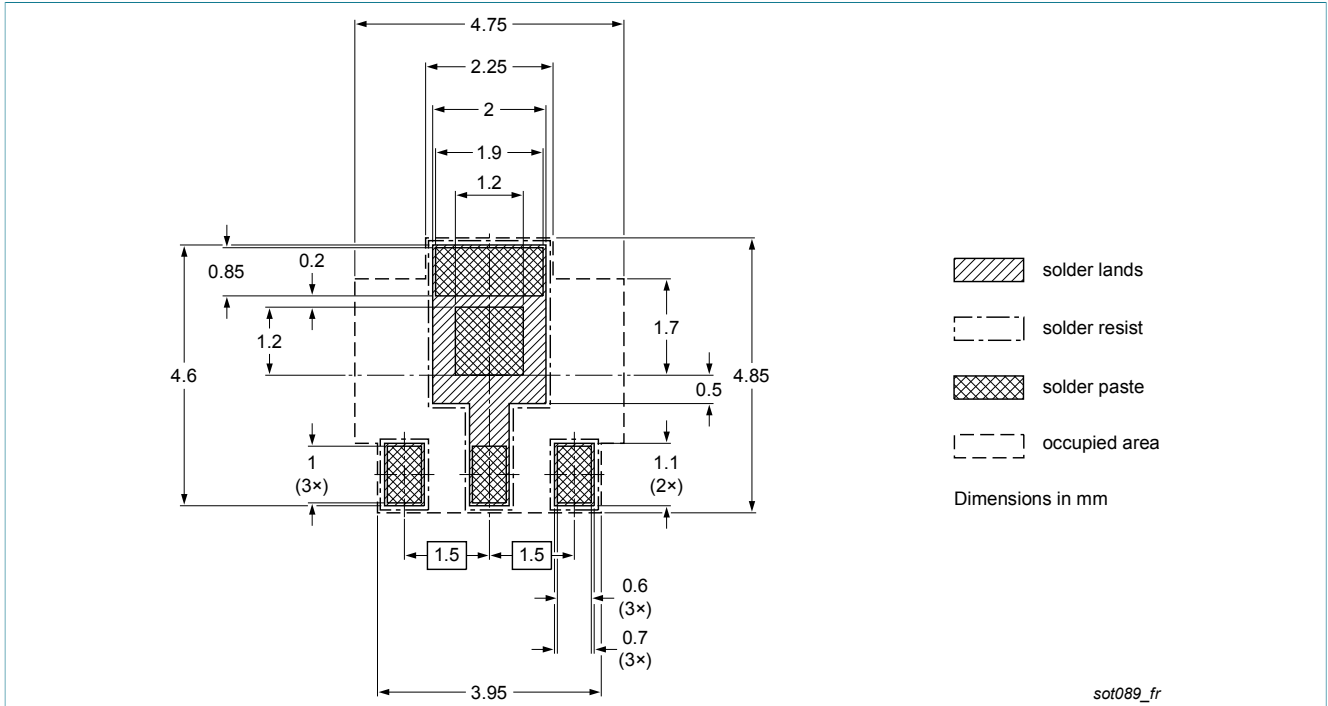


Fig. 19. Reflow soldering footprint for SOT89

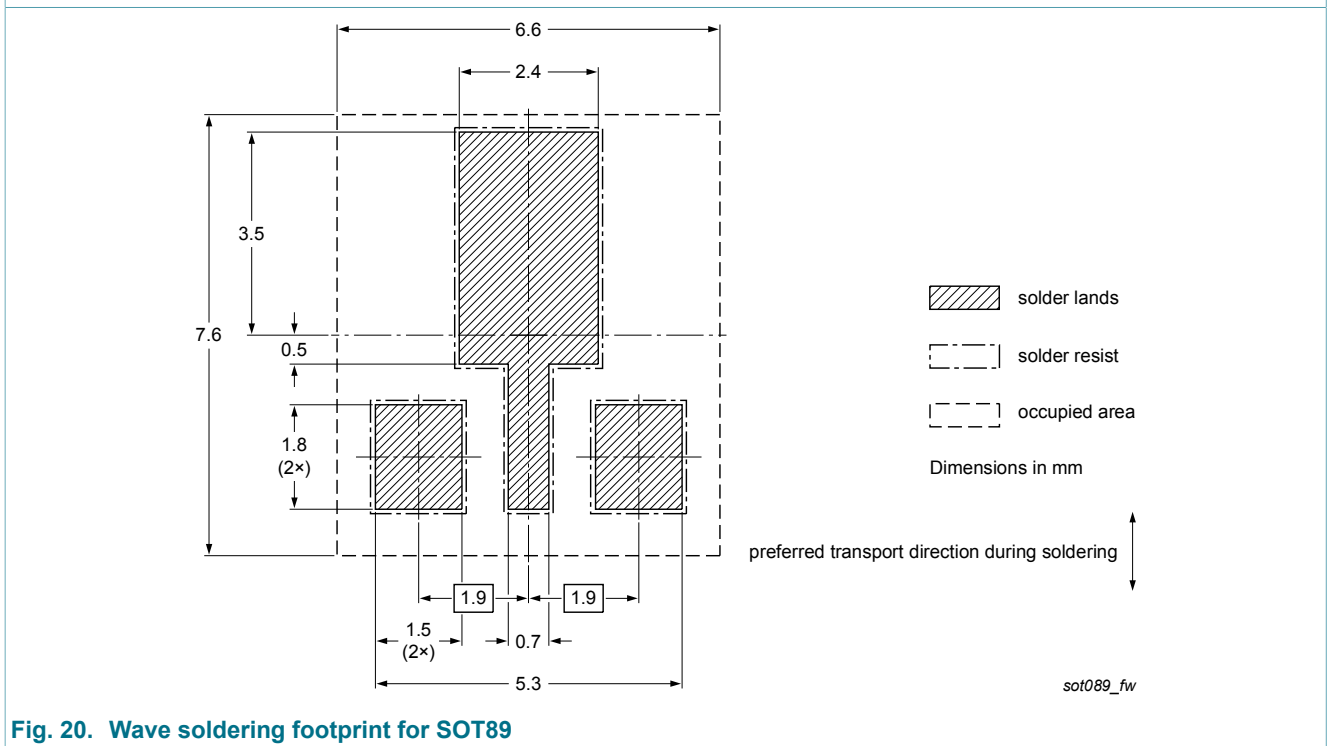


Fig. 20. Wave soldering footprint for SOT89

## 14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BSS87 v.5	20141209	Product data sheet	-	BSS87 v.4
Modifications:	<ul style="list-style-type: none"><li>Figure 3 corrected.</li></ul>			
BSS87 v.4	20140815	Product data sheet	-	BSS87 v.3
BSS87 v.3	20010518	Product specification	-	BSS87 v.2
BSS87 v.2	19970623	Product specification	-	BSS87 v.1

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### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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## 16. Contents

1	General description .....	1
2	Features and benefits .....	1
3	Applications .....	1
4	Quick reference data .....	1
5	Pinning information .....	2
6	Ordering information .....	2
7	Marking .....	2
8	Limiting values .....	3
9	Thermal characteristics .....	5
10	Characteristics .....	7
11	Test information .....	10
12	Package outline .....	11
13	Soldering .....	12
14	Revision history .....	13
15	Legal information .....	14
15.1	Data sheet status .....	14
15.2	Definitions .....	14
15.3	Disclaimers .....	14
15.4	Trademarks .....	15

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